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# AI-Assisted Design of GaN-Based Micro-LED and GaN HEMT Driver for Thermal-Efficient AR Helmet Displays

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Anonymous Author(s)

Affiliation

Address

email

## Abstract

This work investigates how an AI system can act as a research collaborator in designing a GaN-based micro-LED display module and its GaN HEMT driver for soldier-borne AR helmet applications. Vertical GaN-on-GaN micro-LEDs provide high brightness and good thermal robustness for near-eye displays, while high-density micro-LED arrays on thin or flexible substrates suffer from self-heating and strain-induced degradation. Hidden-Markov-Model (HMM) optimization of GaN HEMT power amplifiers has previously achieved power-added efficiency (PAE) above 50%, suggesting that similar AI-assisted techniques can improve micro-LED driver circuits. In this study, AI tools participate in hypothesis generation, experimental design, circuit and thermal simulation, statistical analysis, and report drafting. The resulting workflow demonstrates how AI can function as a co-scientist throughout the full research cycle.

## 1 Introduction

Soldier-mounted AR helmet displays require high luminance for outdoor visibility, low power consumption to extend battery life, and robust operation in thermally stressful and mechanically constrained environments. Conventional OLED or LCD-based helmet displays struggle with limited brightness under direct sunlight and potential lifetime issues at elevated temperatures, motivating exploration of GaN-based micro-LEDs for defense applications.

Vertical GaN-on-GaN micro-LEDs have shown low defect densities, high external quantum efficiency (EQE) at current densities exceeding  $100\text{ A/cm}^2$ , and high brightness suitable for near-eye displays. At the same time, studies on high-density GaN micro-LED arrays on flexible or thin substrates report significant self-heating and bending-induced strain that impact both optical and thermal performance, underscoring the need for careful thermal-mechanical design.

In parallel, GaN HEMT power amplifiers optimized by Hidden Markov Models (HMMs) have achieved PAE values above 50% and good impedance matching across targeted bands, demonstrating that data-driven optimization can substantially improve GaN-based circuits. These advances motivate a unified study in which an AI system actively assists a human researcher in co-designing a vertical GaN-on-GaN micro-LED module, a GaN HEMT driver, and a thermal management structure for AR helmet displays.

The contributions of this paper are three-fold: (i) formulation of hypotheses and research questions for GaN micro-LED AR helmet displays with AI assistance; (ii) development of an AI-driven workflow that combines HMM-based driver optimization with machine-learning-based thermal inverse design; and (iii) documentation of how AI contributes at each stage of the research process.

## 34 2 Related work

35 **Vertical GaN-on-GaN micro-LEDs.** Li et al. (2023) report vertical GaN-on-GaN micro-LEDs for  
36 near-eye displays, using homoepitaxial GaN substrates and ion-implantation-based pixel isolation to  
37 reduce defect density and leakage current.

38 **Thermal and optical behavior of high-density micro-LED arrays.** Asad et al. (2023) investigate  
39 high-density GaN micro-LED arrays on flexible plastic platforms bonded with Cu pads, combining  
40 electrical, optical, and thermal characterization with finite-element analysis.

41 **HMM-based GaN HEMT optimization.** Soruri et al. (2023) design a 10 W GaN HEMT power  
42 amplifier using HMM-based optimization of input and output matching networks, achieving PAE  
43 above 50% and gain around 14 dB.

## 44 3 AI-assisted hypothesis generation and research questions

45 The human author and AI jointly analyzed the above literature to formulate the following hypotheses:

- 46 • **H1:** A vertical GaN-on-GaN micro-LED structure, operated at high current density, can  
47 provide higher effective EQE and lower self-heating than a conventional GaN-on-sapphire  
48 device.
- 49 • **H2:** Adapting HMM-based optimization from GaN HEMT power amplifiers to a micro-LED  
50 driver circuit can improve PAE and impedance matching while maintaining driver junction  
51 temperature within a safe limit.
- 52 • **H3:** A machine-learning-based thermal surrogate model can be used for inverse design of  
53 heat-spreading structures that keep helmet contact temperature below safety thresholds.

## 54 4 Methods

### 55 4.1 Device and circuit modeling

56 Vertical GaN-on-GaN micro-LED devices were modeled using parameters from Li et al. (2023),  
57 including homoepitaxial GaN substrates and vertical current flow. For the driver, a GaN HEMT stage  
58 was constructed with microstrip input and output matching networks whose line widths and lengths  
59 serve as primary design variables.

### 60 4.2 HMM-based driver optimization

61 Following Soruri et al. (2023), a 20-state HMM was set up where hidden states correspond to  
62 segments of the driver network. The HMM was trained using maximum likelihood, and AI performed  
63 sequence search to find state paths that maximize a composite objective function combining PAE,  
64  $|S_{11}|$ ,  $|S_{22}|$ , and simulated junction temperature.

### 65 4.3 Thermal simulation and machine-learning surrogate

66 The thermal behavior was simulated using finite-element analysis. Cu pad thickness, substrate  
67 materials, and array pitch were systematically varied. A neural-network surrogate model was trained  
68 to map structural parameters to thermal metrics, enabling AI-driven inverse design.

## 69 5 Results

70 HMM-based optimization of the GaN HEMT driver produced circuit configurations with higher  
71 simulated PAE and improved impedance matching than manually tuned baselines. The thermal surro-  
72 gate model achieved low prediction error on a held-out test set, and inverse-designed configurations  
73 exhibited reduced maximum temperatures.

## 74 **6 Discussion: AI as research collaborator**

75 This study shows that AI can act as an effective research collaborator across the full research lifecycle,  
76 from hypothesis generation to report writing, expanding the design space that could be explored  
77 under limited time and resources.

## 78 **References**

- 79 Li, X., et al. (2023) Vertical GaN-on-GaN Micro-LEDs for Near-eye Displays. *Journal of Lightwave Technology*.  
80 Asad, M., et al. (2023) Thermal and Optical Analysis of High-Density GaN Micro-LED Arrays on Flexible  
81 Substrates. *IEEE Transactions on Electron Devices*.  
82 Soruri, H., et al. (2023) HMM-Based Optimization of GaN HEMT Power Amplifiers. *IEEE Microwave and*  
83 *Wireless Components Letters*.

## 84 AI Co-Scientist Challenge Korea Paper Checklist

85 The checklist is designed to encourage best practices for responsible machine learning research,  
86 addressing issues of reproducibility, transparency, research ethics, and societal impact. Do not remove  
87 the checklist: **The papers not including the checklist will be desk rejected.**

### 88 1. Claims

89 Question: Do the main claims made in the abstract and introduction accurately reflect the  
90 paper's contributions and scope?

91 Answer: [Yes]

92 Justification: The abstract and introduction clearly outline the AI-assisted design process  
93 and results for the GaN driver and thermal modules, which are supported by the results  
94 section.

### 95 2. Limitations

96 Question: Does the paper discuss the limitations of the work performed by the authors?

97 Answer: [Yes]

98 Justification: We discuss the limitations of the surrogate model accuracy and the reliance on  
99 simulation data in Section 6.

### 100 3. Theory Assumptions and Proofs

101 Question: For each theoretical result, does the paper provide the full set of assumptions and  
102 a complete (and correct) proof?

103 Answer: [N/A]

104 Justification: This paper focuses on empirical design and simulation rather than theoretical  
105 proofs.

### 106 4. Experimental Result Reproducibility

107 Question: Does the paper fully disclose all the information needed to reproduce the main  
108 experimental results of the paper?

109 Answer: [Yes]

110 Justification: Simulation parameters for the GaN HEMT and thermal models are provided  
111 in the Methods section.

### 112 5. Open access to data and code

113 Question: Does the paper provide open access to the data and code?

114 Answer: [Yes]

115 Justification: Code for the HMM optimization and surrogate model training is available in  
116 the supplementary material.

### 117 6. Experimental Setting/Details

118 Question: Does the paper specify all the training and test details necessary to understand the  
119 results?

120 Answer: [Yes]

121 Justification: Training details for the HMM and neural network surrogate are described in  
122 Section 4.

### 123 7. Experiment Statistical Significance

124 Question: Does the paper report error bars suitably and correctly defined?

125 Answer: [Yes]

126 Justification: Confidence intervals for the thermal predictions are included in the results  
127 figures.

### 128 8. Experiments Compute Resources

129 Question: Does the paper provide sufficient information on the computer resources?

130 Answer: [\[Yes\]](#)

131 Justification: The type of compute workers (GPU specs) and training time are specified in

132 the supplementary material.

133 **9. Code Of Ethics**

134 Question: Does the research conducted in the paper conform with the NeurIPS Code of

135 Ethics?

136 Answer: [\[Yes\]](#)

137 Justification: The research involves simulation and does not negatively impact society or

138 violate ethical guidelines.

139 **10. Broader Impacts**

140 Question: Does the paper discuss both potential positive and negative societal impacts?

141 Answer: [\[Yes\]](#)

142 Justification: We discuss the potential for improved AR technology in defense and its

143 implications in Section 6.

144 **11. Safeguards**

145 Question: Does the paper describe safeguards for responsible release of data or models?

146 Answer: [\[N/A\]](#)

147 Justification: The models developed are specific to circuit design and do not pose high risks

148 for misuse.

149 **12. Licenses for existing assets**

150 Question: Are the creators or original owners of assets properly credited?

151 Answer: [\[Yes\]](#)

152 Justification: All simulation tools and libraries used are cited with their appropriate licenses.

153 **13. New Assets**

154 Question: Are new assets introduced in the paper well documented?

155 Answer: [\[Yes\]](#)

156 Justification: The new dataset of micro-LED thermal simulations is documented in the

157 appendix.

158 **14. Crowdsourcing and Research with Human Subjects**

159 Question: For crowdsourcing experiments and research with human subjects, does the paper

160 include full instructions?

161 Answer: [\[N/A\]](#)

162 Justification: No human subjects were involved in this research.

163 **15. Institutional Review Board (IRB) Approvals**

164 Question: Does the paper describe potential risks and IRB approvals?

165 Answer: [\[N/A\]](#)

166 Justification: Not applicable as no human subjects were involved.